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ΡΛΝ	JIT
	SEMI
	CONDUCTOR

### 40V Dual N-Channel Enhancement Mode MOSFET

Current

45 A

Voltage

#### Features

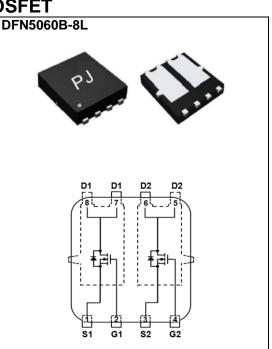
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@15A < 8m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@8A<10.5mΩ

40 V

- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : DFN5060B-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0035 ounces, 0.092 grams



#### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETE	र	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40	N	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V	
$T_{c}=25^{\circ}C$	45				
Continuous Drain Current (Note 4)	Tc=100°C	Ι <sub>D</sub>	28	А	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	180		
Power Dissipation	Tc=25°C	PD	38.5	W	
	T <sub>C</sub> =100°C		19.2		
Continuous Drain Current <sup>(Note 4)</sup> T <sub>A</sub> =25°C T <sub>A</sub> =70°C	T <sub>A</sub> =25°C	Ι <sub>D</sub>	10	^	
	T <sub>A</sub> =70°C		8	A	
Power Dissipation	T <sub>A</sub> =25°C	Po	2.0	W	
	T <sub>A</sub> =70°C		1.4		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	80	mJ	
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	3.9	°C/W	
	Junction to Ambient	R <sub>θJA</sub>	73.5		

• Limited only By Maximum Junction Temperature



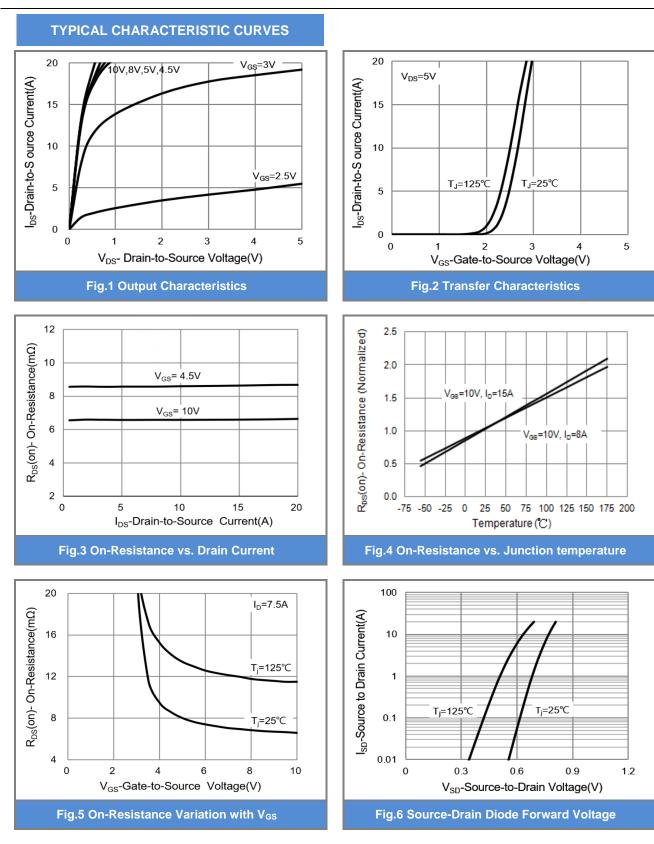
#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		1				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.61	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	6.5	8	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A	-	8	10.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg		-	17	-	nC
Gate-Source Charge	Qgs	$V_{DS}=20V, I_{D}=10A,$	-	4.9	-	
Gate-Drain Charge	Qgd	V <sub>GS</sub> =4.5V (Note 1,2)	-	6.4	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	1759	-	
Output Capacitance	Coss		-	176	-	pF
Reverse Transfer Capacitance	Crss	f=1MHZ	-	126	-	
Turn-On Delay Time	td(on)	$V_{DD}=15V, I_{D}=1A,$ $V_{GS}=10V, R_{G}=6\Omega$ (Note 1,2)	-	11	-	
Turn-On Rise Time	tr		-	21	-	
Turn-Off Delay Time	td(off)		-	40	-	ns
Turn-Off Fall Time	tf		-	25	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					45	•
Diode Forward Current	I <sub>S</sub>		-	-	45	A
Diode Forward Voltage	$V_{SD}$	Is=1A, V <sub>GS</sub> =0V	-	0.7	1	V

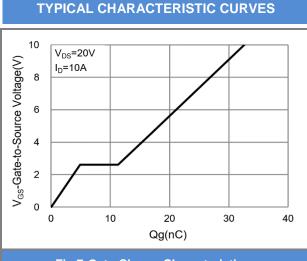
NOTES :

- 1. Pulse width <300us, Duty cycle <2%.
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>®JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =40A,  $V_{DD}$ =25V,  $V_{GS}$ =10V, Starting  $T_J$ =25°C.
- 7. Guaranteed by design, not subject to production testing.











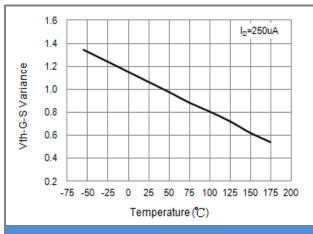
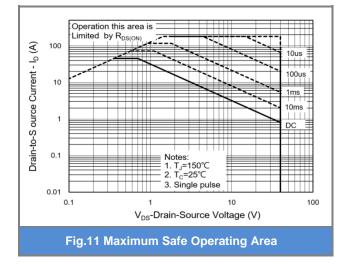
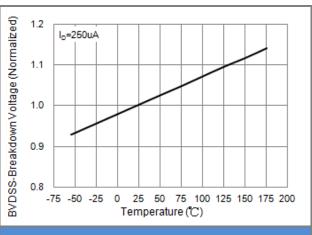


Fig.9 Threshold Voltage Variation with Temperature







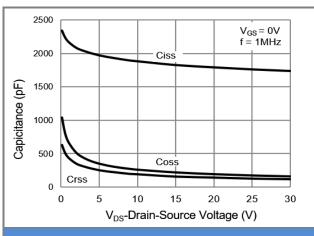
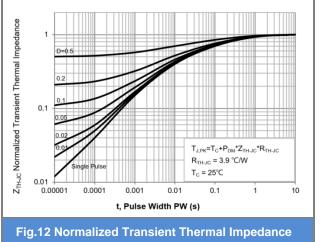


Fig.10 Capacitance vs. Drain-Source Voltage

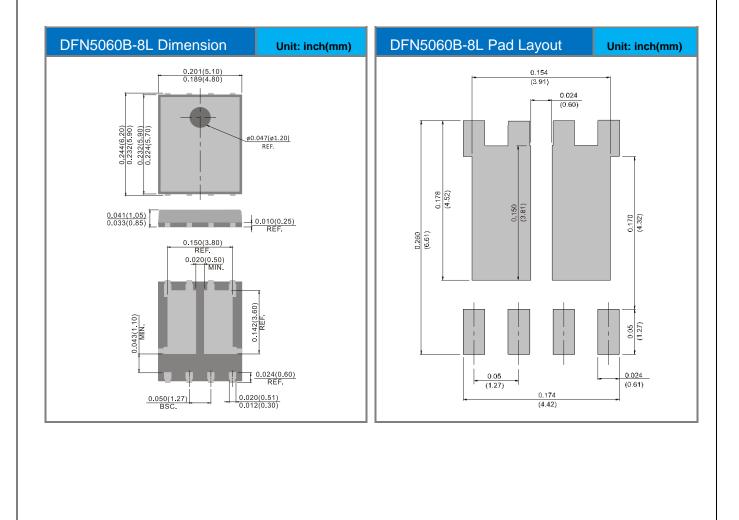




### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ5844-AU	DFN5060B-8L	3000pcs / 13" reel	Q5844	

### Packaging Information & Mounting Pad Layout





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